

# BT131-800E

## 4Q Triac

17 September 2013

Product data sheet

## 1. General description

Planar passivated sensitive gate four quadrant triac in a SOT54 plastic package. This sensitive gate "series E" triac is intended for interfacing with low power drivers including microcontrollers.

## 2. Features and benefits

- Direct interfacing to logic level ICs
- Direct interfacing with low power gate drivers and microcontrollers
- High blocking voltage capability
- Planar passivated for voltage ruggedness and reliability
- Sensitive gate in four quadrants
- Triggering in all four quadrants

## 3. Applications

- Air conditioner indoor fan control
- General purpose low power motor control
- General purpose switching and phase control

## 4. Quick reference data

Table 1. Quick reference data

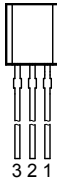
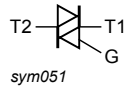
| Symbol                        | Parameter                            | Conditions  | Min | Typ | Max  | Unit |
|-------------------------------|--------------------------------------|---|-----|-----|------|------|
| $V_{DRM}$                     | repetitive peak off-state voltage    |   | -   | -   | 800  | V    |
| $I_{TSM}$                     | non-repetitive peak on-state current | full sine wave; $T_{J(init)} = 25\text{ }^{\circ}\text{C}$ ; $t_p = 20\text{ ms}$ ; <a href="#">Fig. 4</a> ; <a href="#">Fig. 5</a>   | -   | -   | 12.5 | A    |
| $I_{T(RMS)}$                  | RMS on-state current                 | full sine wave; $T_{lead} \leq 51\text{ }^{\circ}\text{C}$ ; <a href="#">Fig. 1</a> ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a> | -   | -   | 1    | A    |
| <b>Static characteristics</b> |                                      |   |     |     |      |      |
| $I_{GT}$                      | gate trigger current                 | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2+ G+; $T_J = 25\text{ }^{\circ}\text{C}$ ; <a href="#">Fig. 7</a>                      | -   | -   | 10   | mA   |
|                               |                                      | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2+ G-; $T_J = 25\text{ }^{\circ}\text{C}$ ; <a href="#">Fig. 7</a>                      | -   | -   | 10   | mA   |
|                               |                                      | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2- G-; $T_J = 25\text{ }^{\circ}\text{C}$ ; <a href="#">Fig. 7</a>                      | -   | -   | 10   | mA   |



| Symbol | Parameter | Conditions  |  | Min | Typ | Max | Unit |
|--------|-----------|---|--|-----|-----|-----|------|
|        |           | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2- G+;<br>$T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 7</a> |  | -   | -   | 10  | mA   |

## 5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description     | Simplified outline   | Graphic symbol  |
|-----|--------|-----------------|--|---|
| 1   | T2     | main terminal 2 |  <p>TO-92 (SOT54)</p> |  |
| 2   | G      | gate            |  |   |
| 3   | T1     | main terminal 1 |  |   |

## 6. Ordering information

Table 3. Ordering information

| Type number | Package |   |         |
|-------------|---------|---|---------|
|             | Name    | Description   | Version |
| BT131-800E  | TO-92   | plastic single-ended leaded (through hole) package; 3 leads | SOT54   |

## 7. Limiting values

**Table 4. Limiting values**

*In accordance with the Absolute Maximum Rating System (IEC 60134).*

| Symbol              | Parameter                            | Conditions  |  | Min | Max  | Unit                   |
|---------------------|--------------------------------------|---|--|-----|------|------------------------|
| $V_{\text{DRM}}$    | repetitive peak off-state voltage    |   |  | -   | 800  | V                      |
| $I_{\text{T(RMS)}}$ | RMS on-state current                 | full sine wave; $T_{\text{lead}} \leq 51\text{ }^{\circ}\text{C}$ ; <a href="#">Fig. 1</a> ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a>        |  | -   | 1    | A                      |
| $I_{\text{TSM}}$    | non-repetitive peak on-state current | full sine wave; $T_{\text{j(init)}} = 25\text{ }^{\circ}\text{C}$ ; $t_{\text{p}} = 20\text{ ms}$ ; <a href="#">Fig. 4</a> ; <a href="#">Fig. 5</a> |  | -   | 12.5 | A                      |
|                     |                                      | full sine wave; $T_{\text{j(init)}} = 25\text{ }^{\circ}\text{C}$ ; $t_{\text{p}} = 16.7\text{ ms}$   |  | -   | 13.7 | A                      |
| $I^2t$              | $I^2t$ for fusing                    | $t_{\text{p}} = 10\text{ ms}$ ; SIN   |  | -   | 0.78 | $\text{A}^2\text{s}$   |
| $dl_{\text{T}}/dt$  | rate of rise of on-state current     | $I_{\text{T}} = 1.5\text{ A}$ ; $I_{\text{G}} = 20\text{ mA}$ ; $dl_{\text{G}}/dt = 0.2\text{ A}/\mu\text{s}$ ; T2+ G+                              |  | -   | 50   | $\text{A}/\mu\text{s}$ |
|                     |                                      | $I_{\text{T}} = 1.5\text{ A}$ ; $I_{\text{G}} = 20\text{ mA}$ ; $dl_{\text{G}}/dt = 0.2\text{ A}/\mu\text{s}$ ; T2+ G-                              |  | -   | 50   | $\text{A}/\mu\text{s}$ |
|                     |                                      | $I_{\text{T}} = 1.5\text{ A}$ ; $I_{\text{G}} = 20\text{ mA}$ ; $dl_{\text{G}}/dt = 0.2\text{ A}/\mu\text{s}$ ; T2- G-                              |  | -   | 50   | $\text{A}/\mu\text{s}$ |
|                     |                                      | $I_{\text{T}} = 1.5\text{ A}$ ; $I_{\text{G}} = 20\text{ mA}$ ; $dl_{\text{G}}/dt = 0.2\text{ A}/\mu\text{s}$ ; T2- G+                              |  | -   | 10   | $\text{A}/\mu\text{s}$ |
| $I_{\text{GM}}$     | peak gate current                    |   |  | -   | 2    | A                      |
| $P_{\text{GM}}$     | peak gate power                      |   |  | -   | 5    | W                      |
| $P_{\text{G(AV)}}$  | average gate power                   | over any 20 ms period   |  | -   | 0.1  | W                      |
| $T_{\text{stg}}$    | storage temperature                  |   |  | -40 | 150  | $^{\circ}\text{C}$     |
| $T_{\text{j}}$      | junction temperature                 |   |  | -   | 125  | $^{\circ}\text{C}$     |

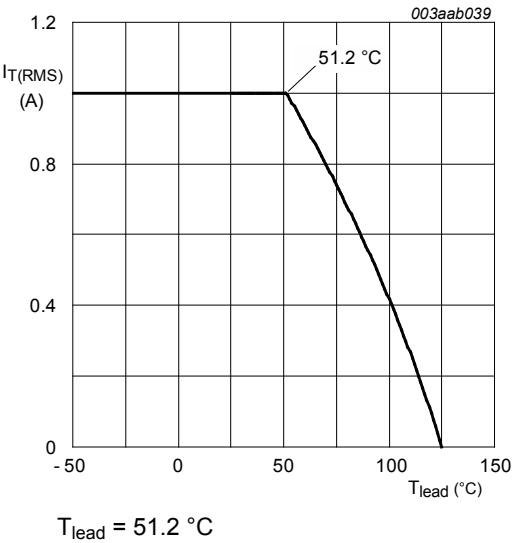


Fig. 1. RMS on-state current as a function of lead temperature; maximum values

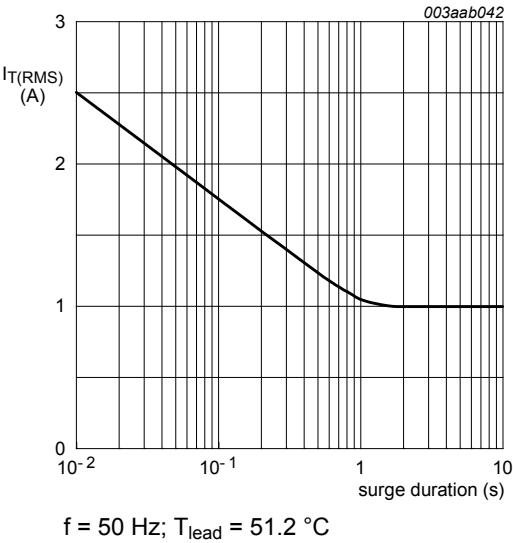


Fig. 2. RMS on-state current as a function of surge duration; maximum values

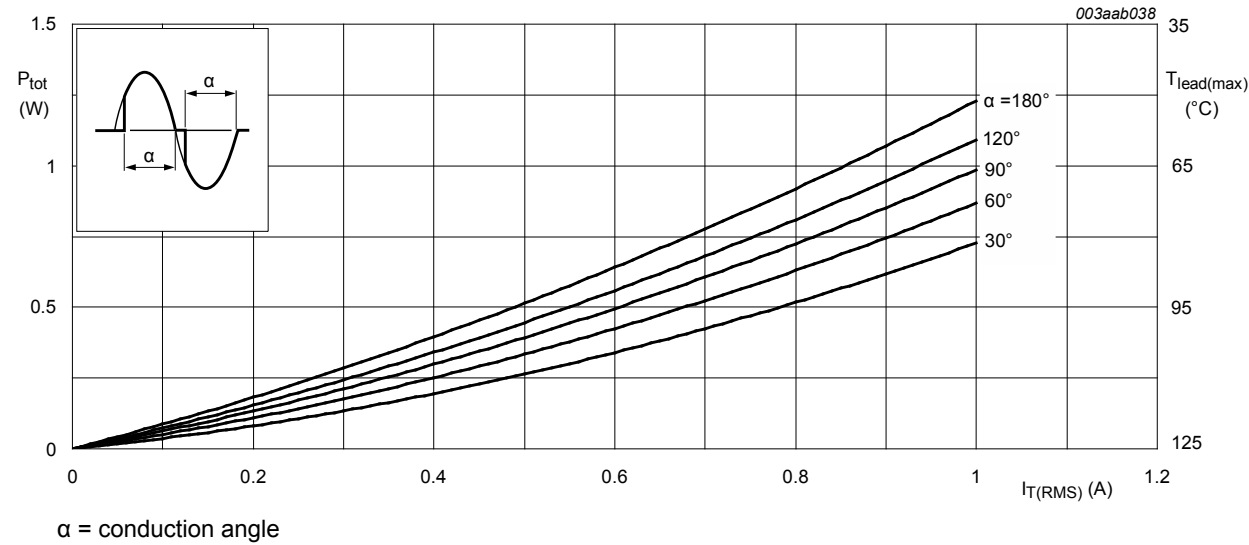


Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

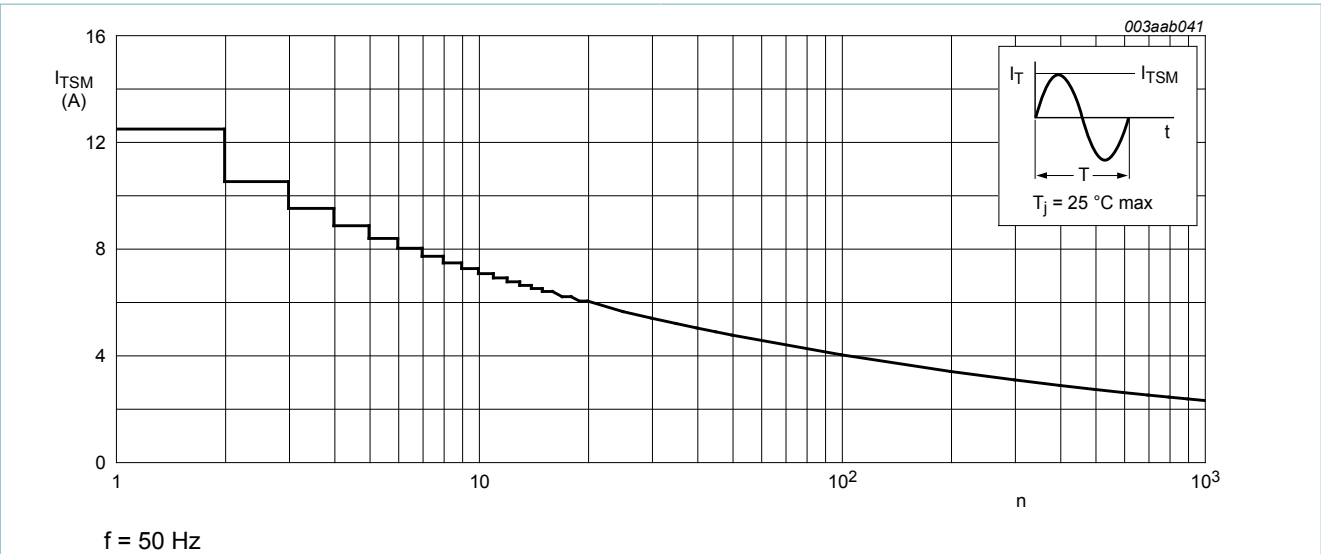


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

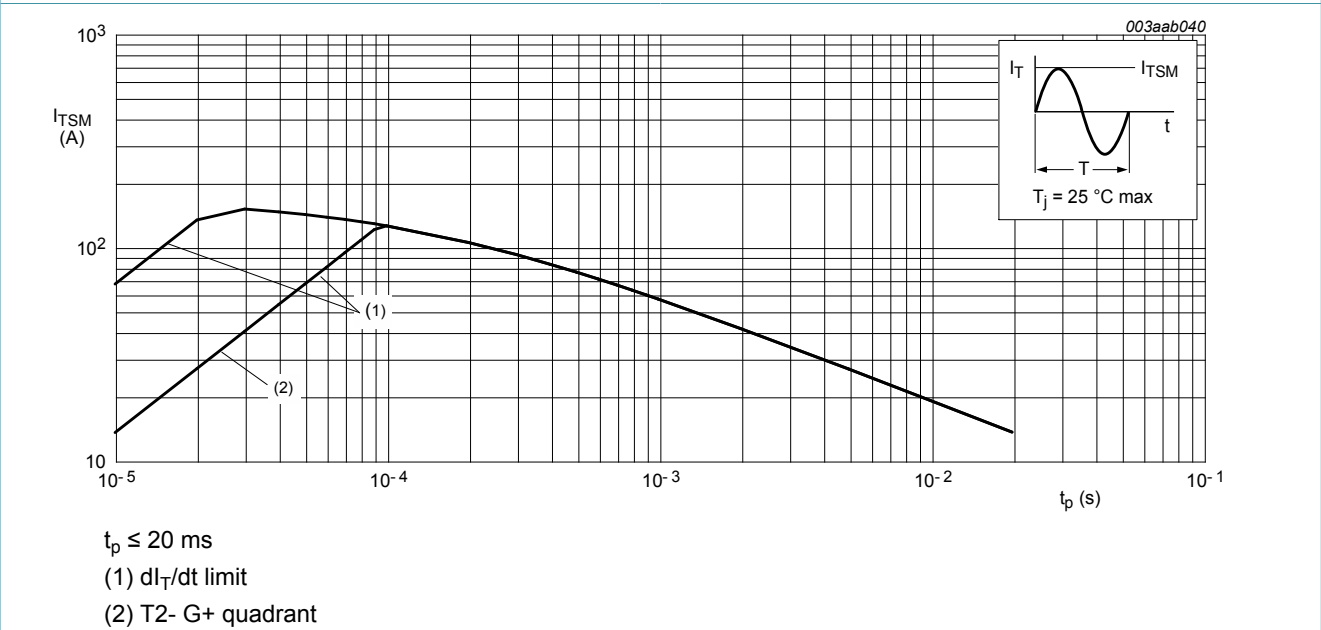
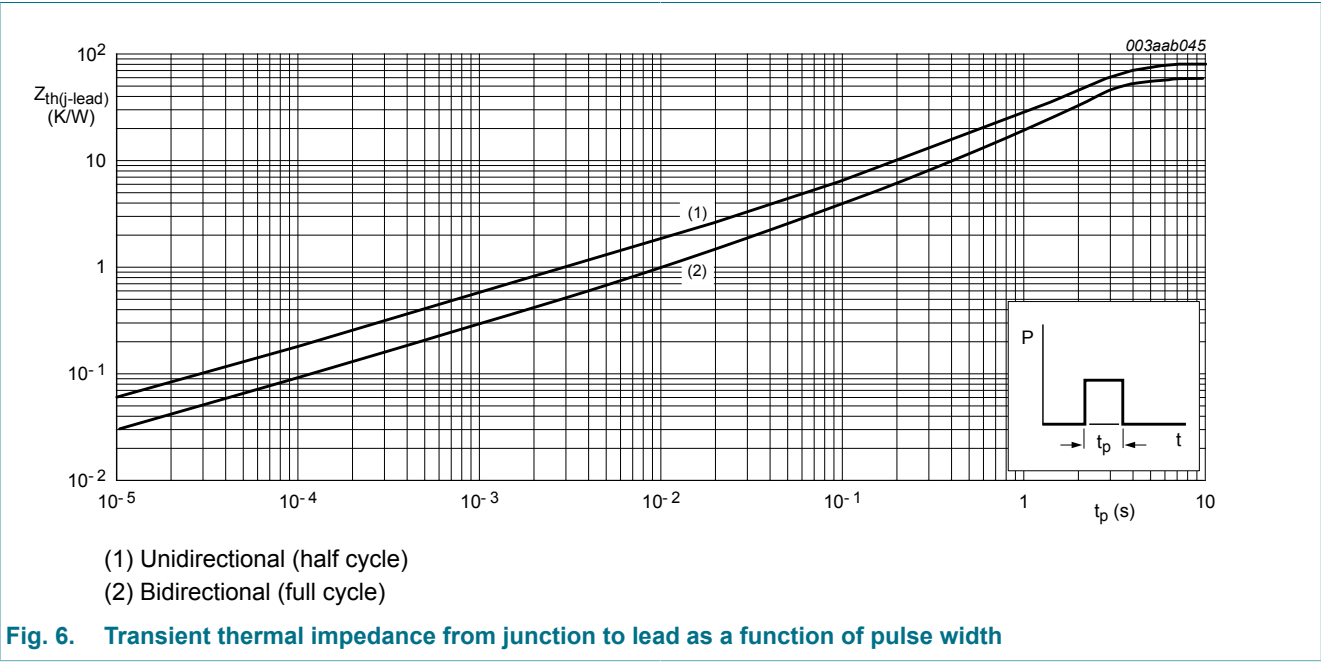


Fig. 5. Non-repetitive peak on-state current as a function of pulse width for sinusoidal currents; maximum values

8. Thermal characteristics

Table 5. Thermal characteristics

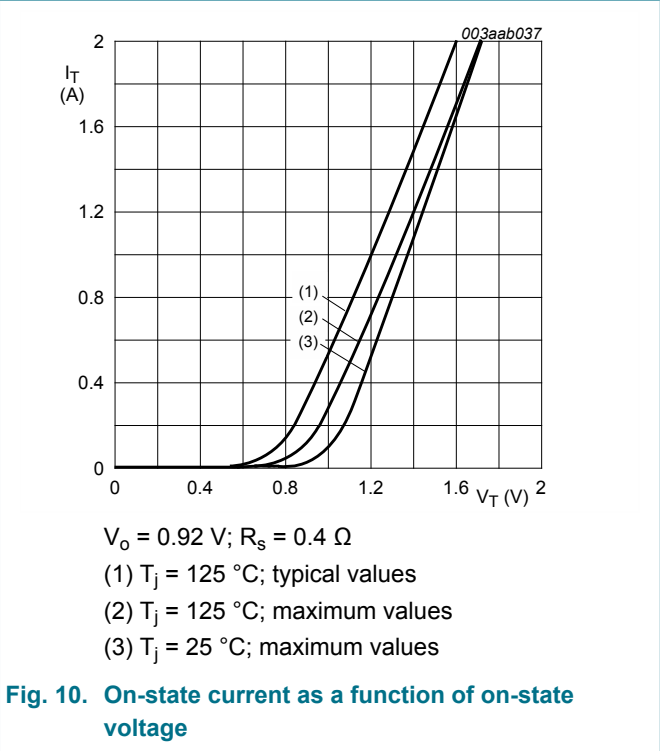
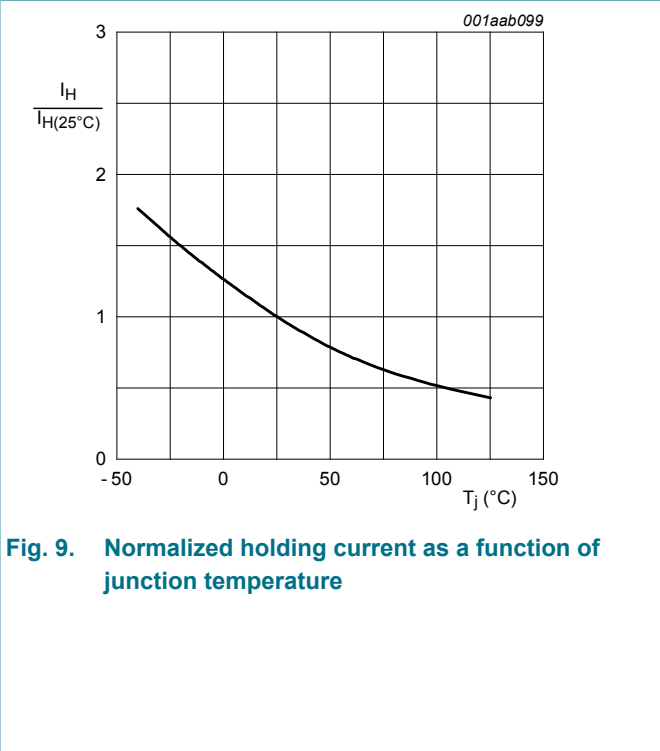
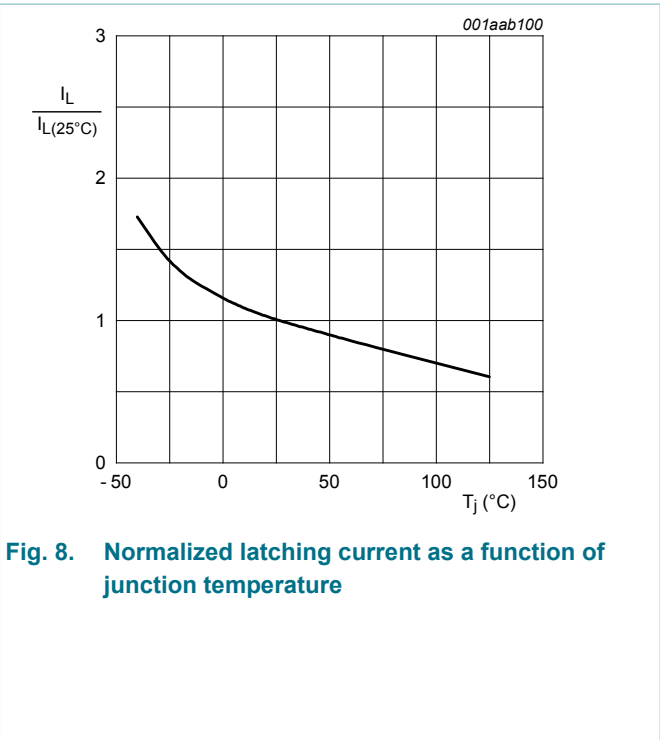
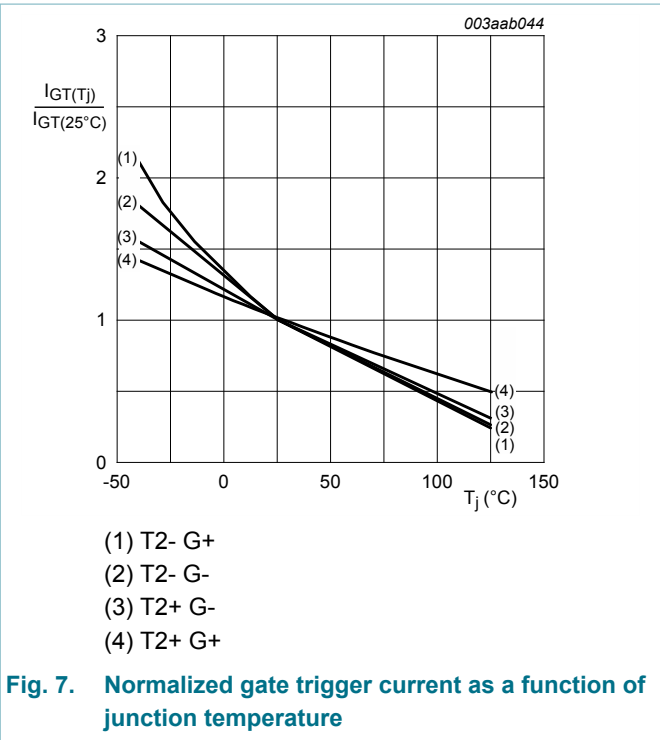
| Symbol           | Parameter                                   | Conditions  | Min | Typ | Max | Unit |
|------------------|---|---|-----|-----|-----|------|
| $R_{th(j-lead)}$ | thermal resistance from junction to lead    | full cycle; Fig. 6                                | -   | -   | 60  | K/W  |
|                  |   | half cycle; Fig. 6                                | -   | -   | 80  | K/W  |
| $R_{th(j-a)}$    | thermal resistance from junction to ambient | printed circuit board mounted: lead length = 4 mm | -   | 150 | -   | K/W  |



## 9. Characteristics

Table 6. Characteristics

| Symbol                         | Parameter                             | Conditions   | Min | Typ | Max | Unit             |
|--------------------------------|---------------------------------------|--|-----|-----|-----|------------------|
| <b>Static characteristics</b>  |                                       |  |     |     |     |                  |
| $I_{GT}$                       | gate trigger current                  | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2+ G+;<br>$T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 7</a>                                      | -   | -   | 10  | mA               |
|                                |                                       | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2+ G-;<br>$T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 7</a>                                      | -   | -   | 10  | mA               |
|                                |                                       | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2- G-;<br>$T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 7</a>                                      | -   | -   | 10  | mA               |
|                                |                                       | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2- G+;<br>$T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 7</a>                                      | -   | -   | 10  | mA               |
| $I_L$                          | latching current                      | $V_D = 12\text{ V}$ ; $I_G = 0.1\text{ A}$ ; T2+ G+;<br>$T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 8</a>                                      | -   | -   | 15  | mA               |
|                                |                                       | $V_D = 12\text{ V}$ ; $I_G = 0.1\text{ A}$ ; T2+ G-;<br>$T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 8</a>                                      | -   | -   | 15  | mA               |
|                                |                                       | $V_D = 12\text{ V}$ ; $I_G = 0.1\text{ A}$ ; T2- G-;<br>$T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 8</a>                                      | -   | -   | 25  | mA               |
|                                |                                       | $V_D = 12\text{ V}$ ; $I_G = 0.1\text{ A}$ ; T2- G+;<br>$T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 8</a>                                      | -   | -   | 15  | mA               |
| $I_H$                          | holding current                       | $V_D = 12\text{ V}$ ; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 9</a>  | -   | 1.3 | 10  | mA               |
| $V_T$                          | on-state voltage                      | $I_T = 1.4\text{ A}$ ; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 10</a>  | -   | 1.2 | 1.5 | V                |
| $V_{GT}$                       | gate trigger voltage                  | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; $T_j = 25\text{ }^\circ\text{C}$ ;<br><a href="#">Fig. 11</a>   | -   | 0.7 | 1   | V                |
|                                |                                       | $V_D = 400\text{ V}$ ; $I_T = 0.1\text{ A}$ ; $T_j = 125\text{ }^\circ\text{C}$ ;<br><a href="#">Fig. 11</a>   | 0.2 | 0.3 | -   | V                |
| $I_D$                          | off-state current                     | $V_D = 800\text{ V}$ ; $T_j = 125\text{ }^\circ\text{C}$   | -   | 0.1 | 0.5 | mA               |
| <b>Dynamic characteristics</b> |                                       |  |     |     |     |                  |
| $dV_D/dt$                      | rate of rise of off-state voltage     | $V_{DM} = 536\text{ V}$ ; $T_j = 125\text{ }^\circ\text{C}$ ; $R_{GT1} = 1\text{ k}\Omega$ ;<br>( $V_{DM} = 67\%$ of $V_{DRM}$ ); exponential waveform | 50  | -   | -   | V/ $\mu\text{s}$ |
| $dV_{com}/dt$                  | rate of change of commutating voltage | $V_D = 400\text{ V}$ ; $T_j = 125\text{ }^\circ\text{C}$ ; $dI_{com}/dt = 0.5\text{ A/ms}$ ; $I_T = 1\text{ A}$ ; gate open circuit                    | 5   | -   | -   | V/ $\mu\text{s}$ |
| $t_{gt}$                       | gate-controlled turn-on time          | $I_{TM} = 1.5\text{ A}$ ; $V_D = 800\text{ V}$ ; $I_G = 0.1\text{ A}$ ; $dI_G/dt = 5\text{ A}/\mu\text{s}$   | -   | 2   | -   | $\mu\text{s}$    |





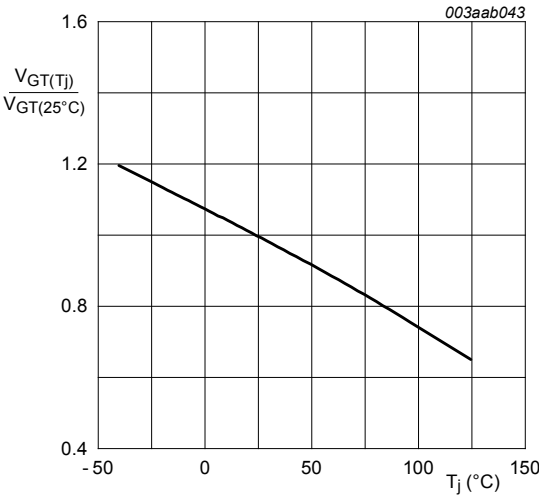


Fig. 11. Normalized gate trigger voltage as a function of junction temperature

10. Package outline

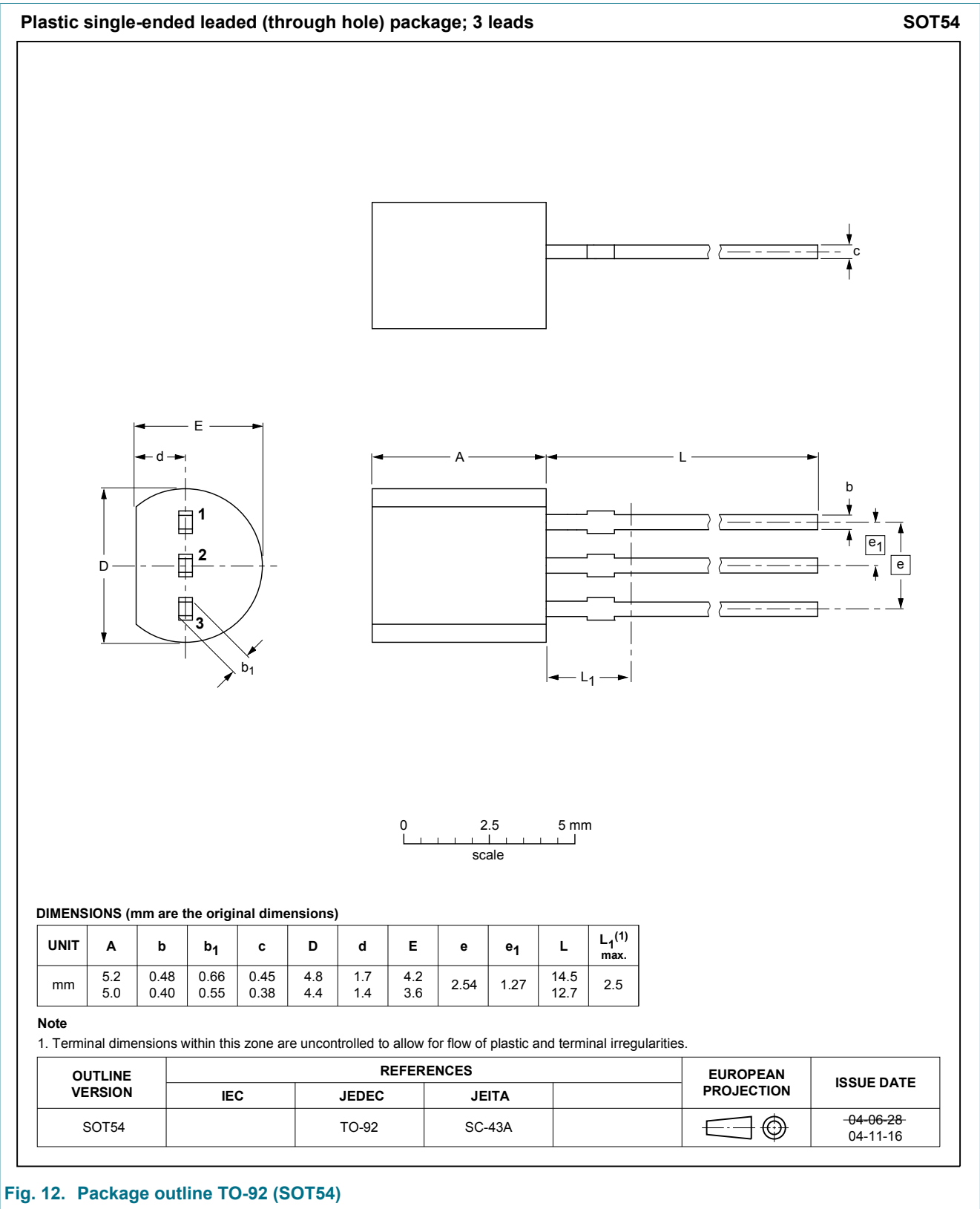


Fig. 12. Package outline TO-92 (SOT54)

## 11. Legal information

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| Document status [1][2]         | Product status [3] | Definition  |
|--------------------------------|--------------------|---|
| Objective [short] data sheet   | Development        | This document contains data from the objective specification for product development. |
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